

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a semiconductor substrate of a first conductivity type, in which an extended drain region of a second conductivity type and a source region of the second conductivity type are formed with an interval therebetween, wherein the extended drain region includes a plurality of buried layers, each formed by burying an impurity layer of the first conductivity type, the plurality of buried layers extending substantially parallel to a substrate surface and with an interval therebetween in a depth direction. A concentration of an impurity of the second conductivity type in the extended drain region at a depth of about 6 μm from the substrate surface is about $1 \times 10^{15}/\text{cm}^3$ or more and is about 30% or more of that at a depth of about 2 μm from the substrate surface.